



Description

The SH8J66TB1 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

$V_{DS} = -30V, I_D = -11A$

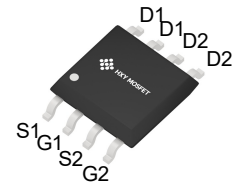
$R_{DS(ON)} < 18m @ V_{GS} = -10V$

$R_{DS(ON)} < 27m @ V_{GS} = -4.5V$

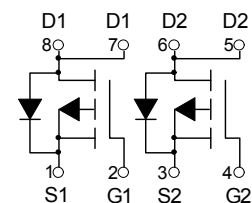
Application

PWM application

Load switch



SOP-8



Dual P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SH8J66TB1	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	-11	A
I_{DM}	Drain Current-Pulsed (Note 1)	-40	A
P_D	Maximum Power Dissipation	3.7	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	33.8	$^{\circ}C/W$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} =0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance Note3	V _{GS} = -10V, I _D = -10A	-	14	18	mΩ
		V _{GS} = -4.5V, I _D = -5A	-	20	27	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} =0V, f=1.0MHz	-	1330	-	pF
C _{oss}	Output Capacitance		-	183	-	pF
C _{rss}	Reverse Transfer Capacitance		-	156	-	pF
Q _g	Total Gate Charge	V _{DS} = -15V, I _D = -5A, V _{GS} = -10V	-	22	-	nC
Q _{gs}	Gate-Source Charge		-	1.0	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	1.8	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -10A, V _{GS} =-10V, R _{GEN} =2.5Ω	-	9	-	ns
t _r	Turn-on Rise Time		-	13	-	ns
t _{d(off)}	Turn-off Delay Time		-	48	-	ns
t _f	Turn-off Fall Time		-	20	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-11	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -15A	-	-0.8	-1.2	V
t _{rr}	Reverse Recovery Time	T _J =25°C,	-	64	-	ns
Q _{rr}	Reverse Recovery Charge	V _{DD} = -24V, I _F =-2.8A, dI/dt=-100A/μs	-	25	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25°C, V_{GS}=10V, R_G=25Ω, L=0.5mH, I_{AS}=-12.7A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure1: Output Characteristics

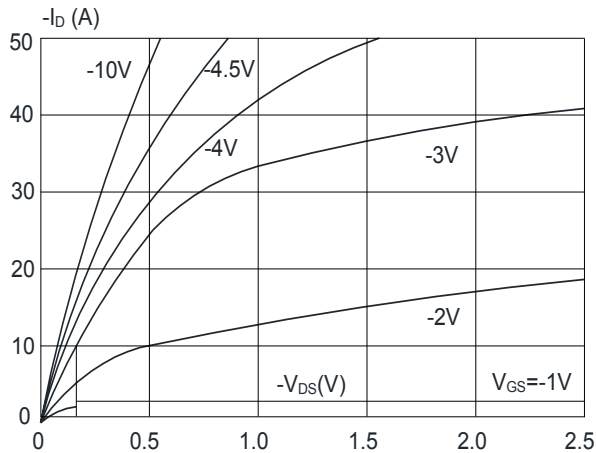


Figure 2: Typical Transfer Characteristics

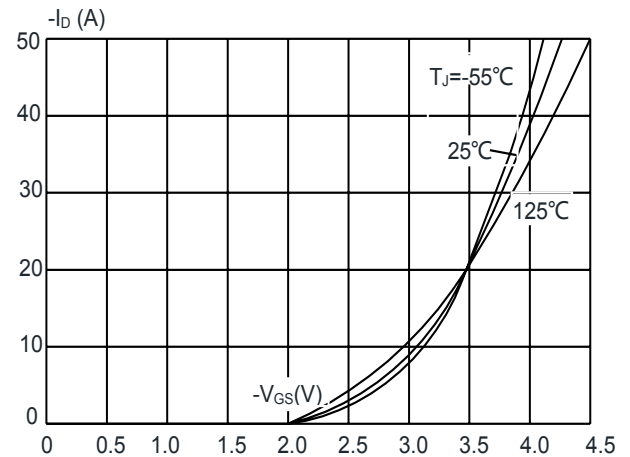


Figure 3: On-resistance vs. Drain Current

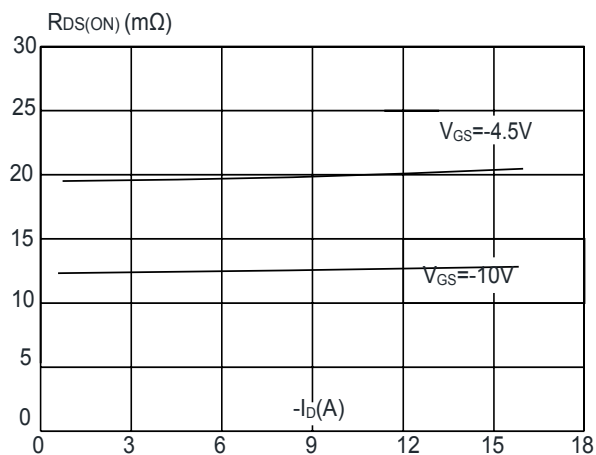


Figure 4: Body Diode Characteristics

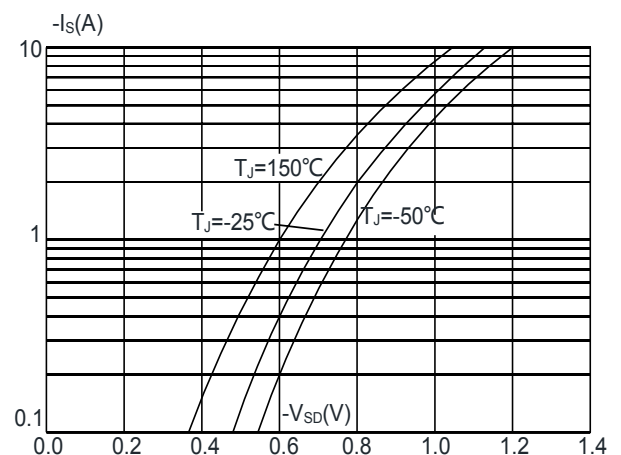


Figure 5: Gate Charge Characteristics

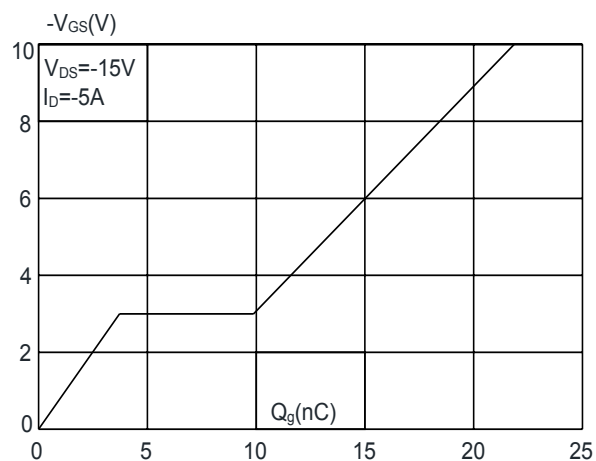


Figure 6: Capacitance Characteristics

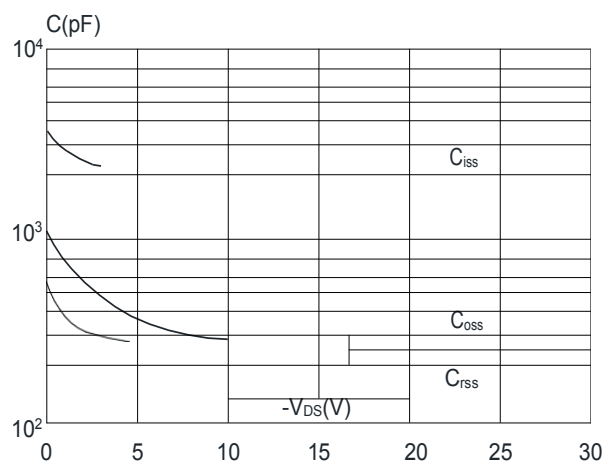




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

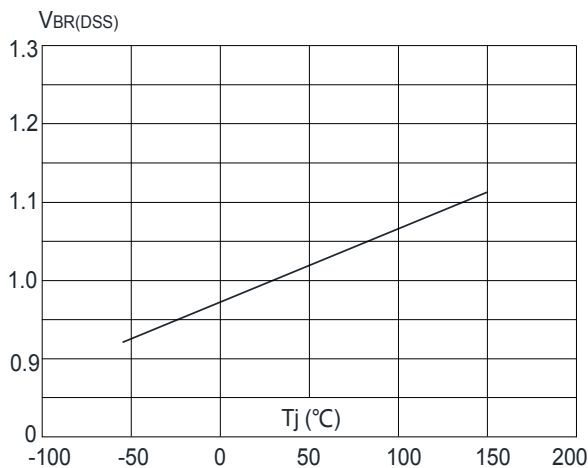


Figure 8: Normalized on Resistance vs. Junction Temperature

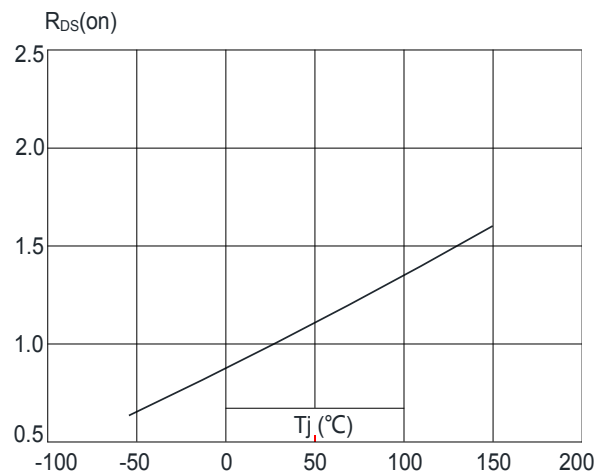


Figure 9: Maximum Safe Operating Area

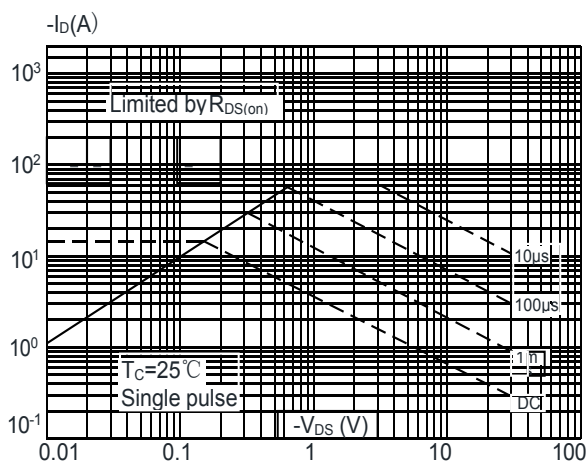


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

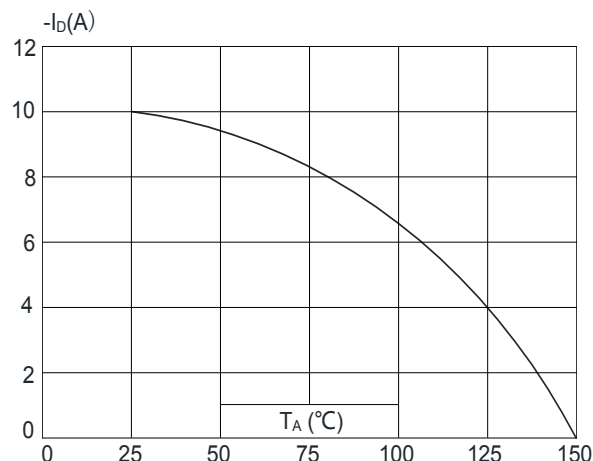
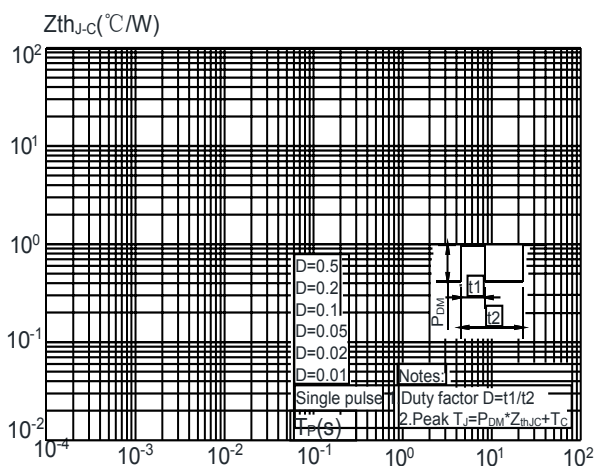


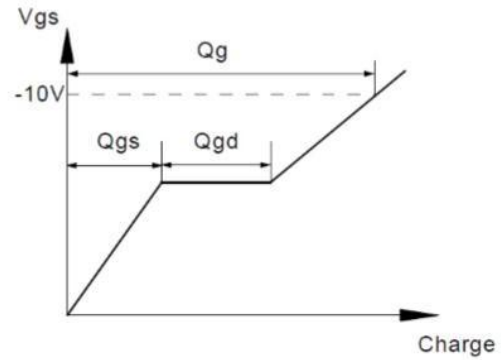
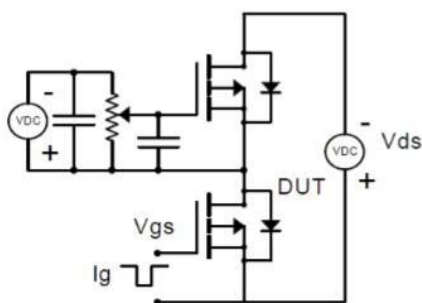
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



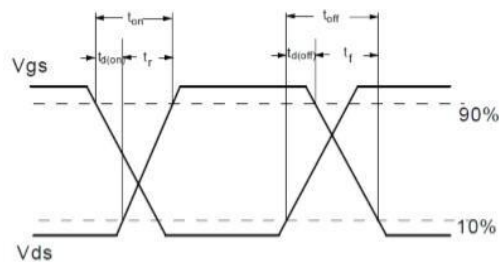
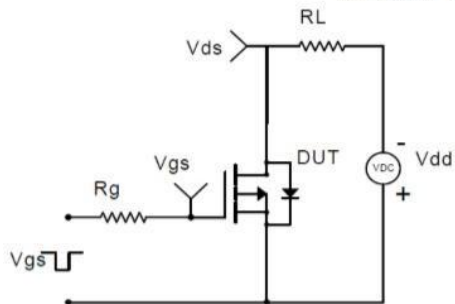


Test Circuit

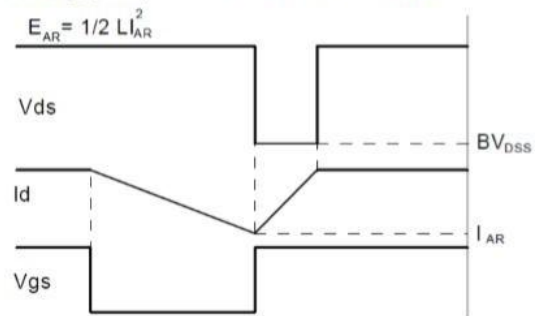
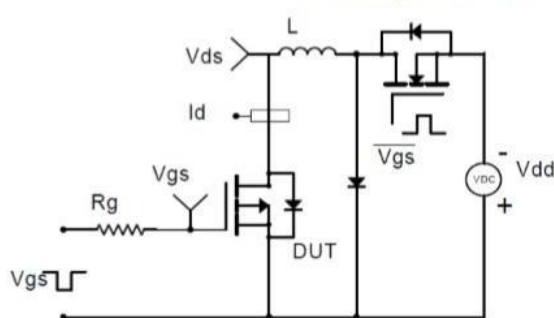
Gate Charge Test Circuit & Waveform



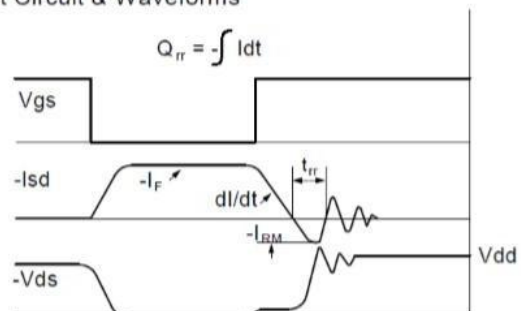
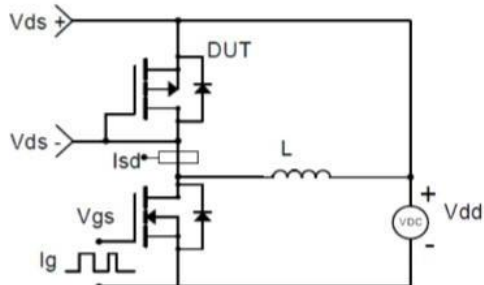
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

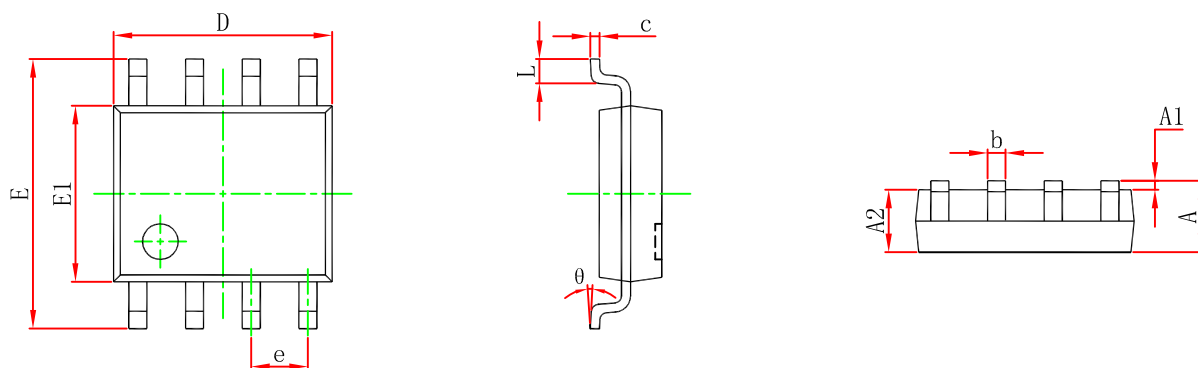


Diode Recovery Test Circuit & Waveforms

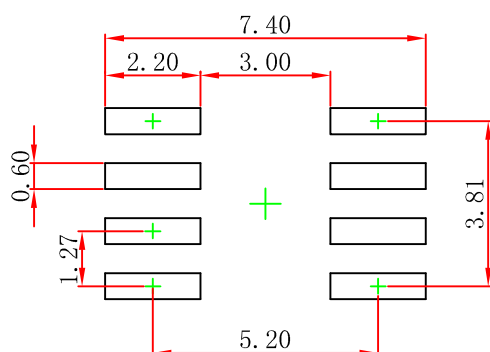




SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.



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